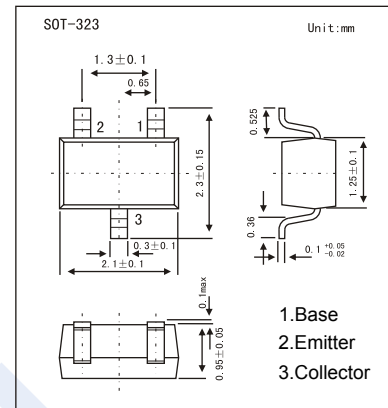


PNP Transistors

2SA1587

■ Features

- High voltage
- Low noise
- Complementary to 2SC4117
- Small Package



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-120	V
Collector - Emitter Voltage	V_{CE0}	-120	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-100	mA
Base Current	I_B	-20	
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}, I_E = 0$	-120			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 \text{ mA}, I_B = 0$	-120			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -120 \text{ V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$			-0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -6 \text{ V}, I_C = -2 \text{ mA}$	200		700	
Noise figure	NF	$V_{CE} = -6 \text{ V}, I_C = 0.1 \text{ mA}, f = 1 \text{ kHz}, R_g = 10 \text{ K}\Omega$		1	10	dB
Collector output capacitance	C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4		pF
Transition frequency	f_T	$V_{CE} = -6 \text{ V}, I_C = -1 \text{ mA}$		100		MHz

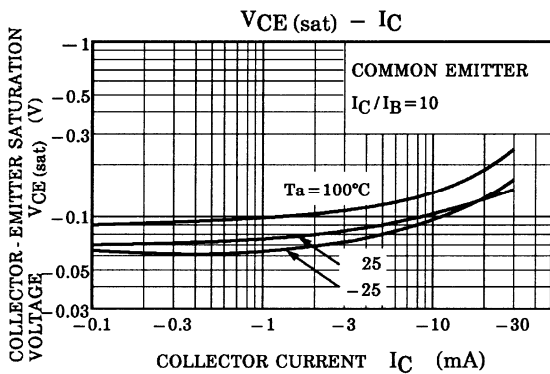
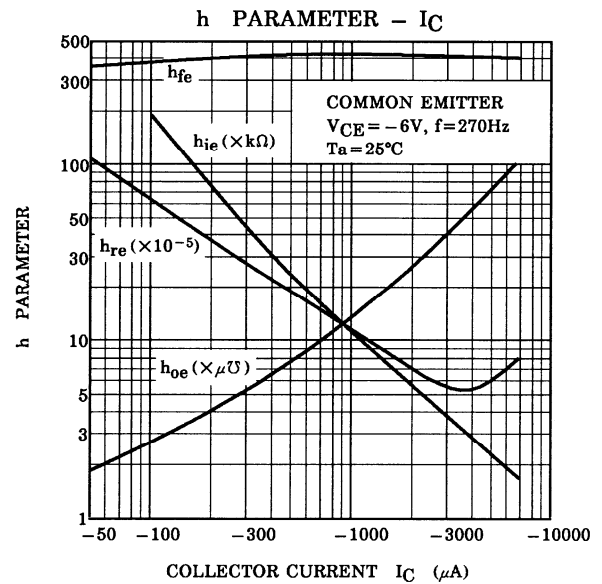
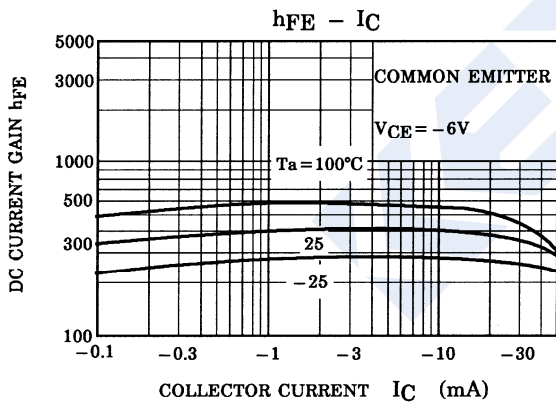
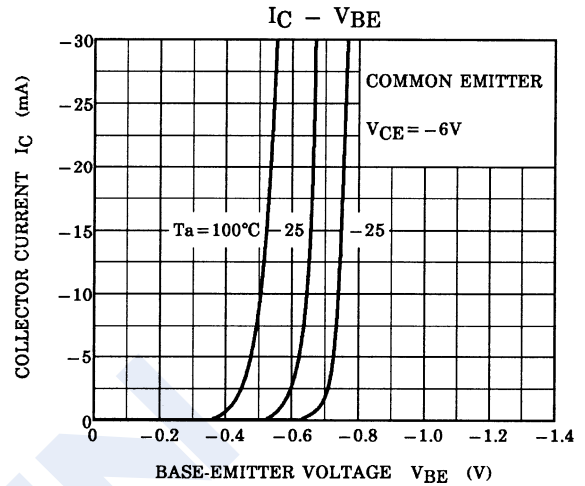
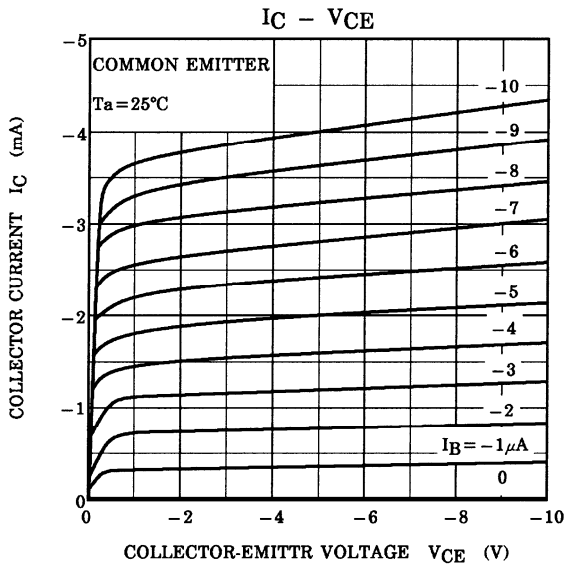
■ Classification of h_{fe}

Type	2SA1587-G	2SA1587-L
Range	200-400	350-700
Marking	CG	CL

PNP Transistors

2SA1587

■ Typical Characteristics



PNP Transistors

2SA1587

■ Typical Characteristics

